ShiLing® 浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

产品规格书

Specifcation of products

产品名称:快恢复二极管

产品型号:MF2X100U12NK5

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ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

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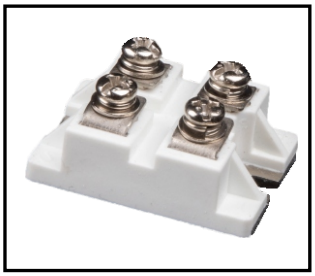
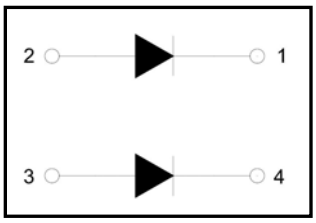
拟制	审核	核准
林益龙	曹剑龙	宗瑞

版本号:05 更新日期:2023.8

PRODUCT FEATURES

- Ultrafast Reverse Recovery Time
- Soft Reverse Recovery Characteristics
- Low Reverse Recovery Loss
- High System Power Density
- Popular SOT-227 Package





APPLICATIONS

- Inversion Welder
- Uninterruptible Power Supply (UPS)
- Plating Power Supply
- Ultrasonic Cleaner and Welder
- Converter & Chopper
- Power Factor Correction (PFC) Circuit

ABSOLUTE MAXIMUM RATINGS

T_C=25℃ unless otherwise specified

Symbol	Parameter	Test Conditions	Values	Unit
V_R	Maximum D.C. Reverse Voltage		1200	V
V_{RRM}	Maximum Repetitive Reverse Voltage		1200	V
$I_{F(AV)}$	Average Forward Current	T_C=90℃, Per Diode	100	A
		T_C=90℃, Per Moudle	200	A
$I_{F(RMS)}$	RMS Forward Current	T_C=90℃, Per Diode	141	A
I_{FSM}	Non-Repetitive Surge Forward Current	T_J=45℃, t=10ms, 50Hz, Sine	1450	A
		T_J=45℃, t=8.3ms, 60Hz, Sine	1600	A
I^2t	I^2t (For Fusing)	T_J=45℃, t=10ms, 50Hz, Sine	10512	A^2s
		T_J=45℃, t=8.3ms, 60Hz, Sine	12800	A^2s
P_D	Power Dissipation		278	W
T_J	Junction Temperature		-40 to +150	℃
T_{STG}	Storage Temperature Range		-40 to +125	℃
V_{isol}	Insulation Test Voltage	AC, t=1min	3000	V
Torque	To-Sink	Recommended（M4）	0.7～1.1	N.m
Torque	To-Terminal	Recommended（M4）	0.7～1.1	N.m
$R_{\theta JC}$	Thermal Resistance	Junction-to-Case	0.45	℃ /W
Weight			26.5	g

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{RM}	Reverse Leakage Current	V_R=1200V	--	--	0.5	mA
		V_R=1200V, T_J=125℃	--	--	2	mA
V_F	Forward Voltage	I_F=100A	--	1.6	--	V
		I_F=100A, T_J =125℃	--	1.38	--	V
t_{rr}	Reverse Recove ry T ėm	I_F=1A, V_R=30V, di_F/dt=-200A/μs	--	50	--	ns
t_{rr}	Reverse Recove ry T ėm	V_R=600V, I_F=100A	--	135	--	ns
I_{RRM}	Max. Reverse Recovery Curre	di_F/dt=-200A/μs, T_J=25℃	--	10	--	A
t_{rr}	Reverse Recovery Time	V_R=600V, I_F=100A	--	380	--	ns
I_{RRM}	Max. Reverse Recovery Current	di_F/dt=-200A/μs, T_J=125℃	--	21	--	A

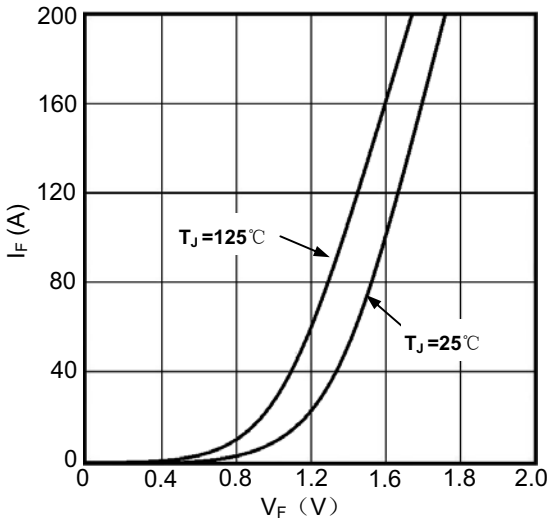


Figure1. Forward Voltage Drop vs Forward Current

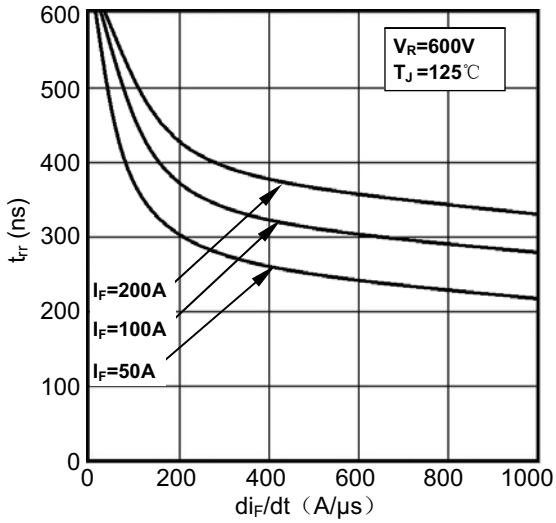


Figure2. Reverse Recovery Time vs di_F/dt

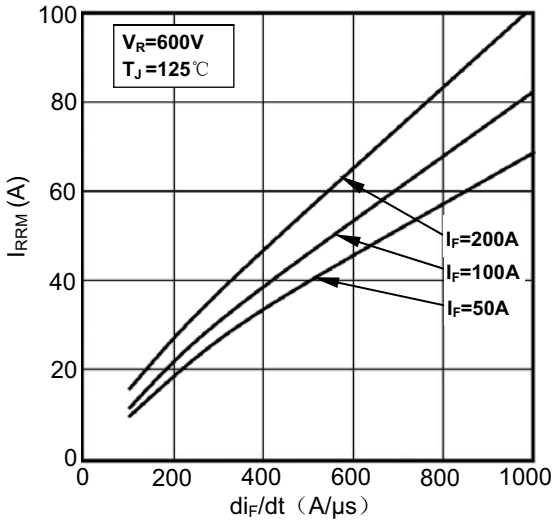


Figure3. Reverse Recovery Current vs di_F/dt

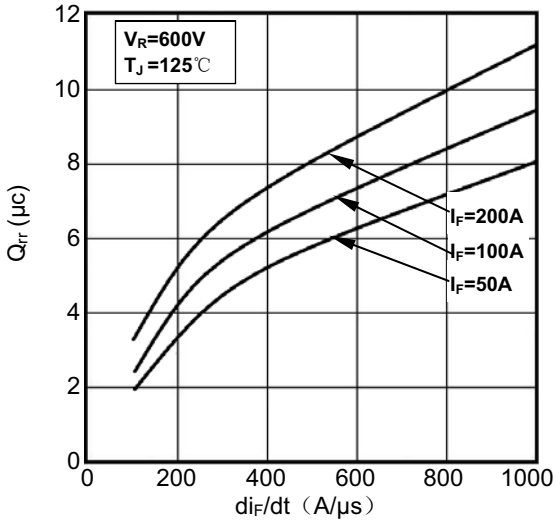


Figure4. Reverse Recovery Charge vs di_F/dt

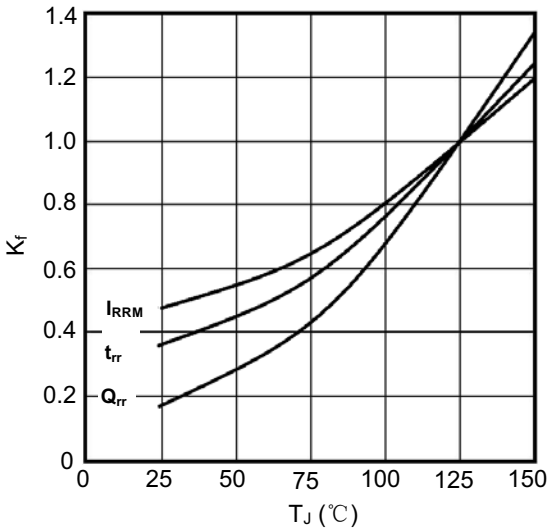
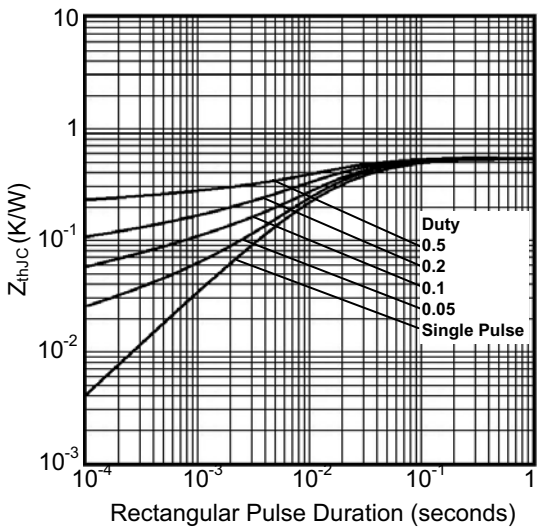


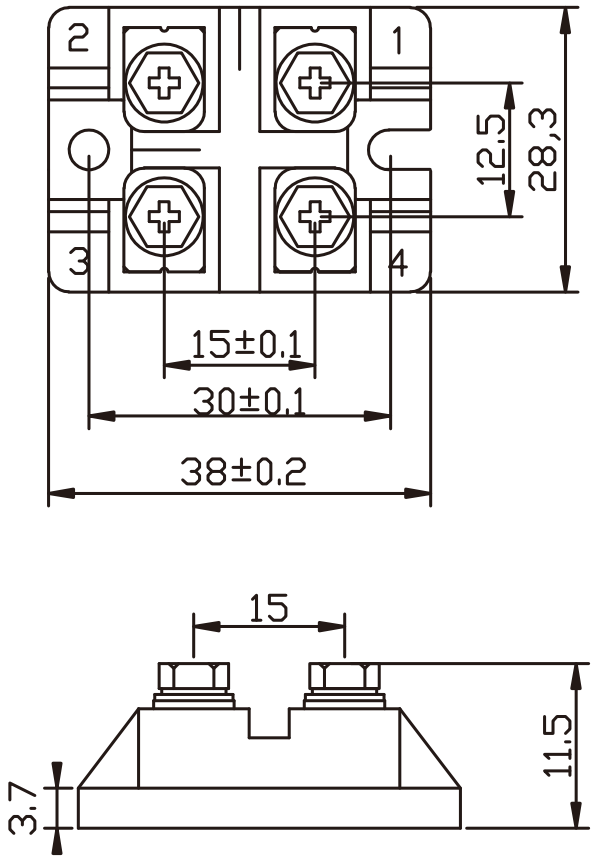
Figure5. Dynamic Parameters vs Junction Temperature



Rectangular Pulse Duration (seconds)

Figure6. Transient Thermal Impedance

Package Outline



Dimensions (mm)